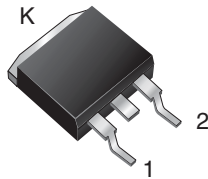
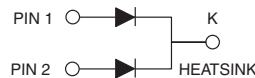


## Dual Common Cathode Schottky Rectifier

High Barrier Technology for Improved High Temperature Performance

**D<sup>2</sup>PAK (TO-263AB)**

**MBRB25HxxCT**


### DESIGN SUPPORT TOOLS

**3D**  
Models  
Available

[click logo to get started](#)

### FEATURES

- Power pack
- Guardring for overvoltage protection
- Lower power losses, high efficiency
- Low forward voltage drop
- Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

### TYPICAL APPLICATIONS

For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters, or polarity protection application.

### MECHANICAL DATA

**Case:** D<sup>2</sup>PAK (TO-263AB)

Molding compound meets UL 94 V-0 flammability rating  
Base P/NHE3\_X - RoHS-compliant, AEC-Q101 qualified  
("X" denotes revision code, e.g. A, B, ...)

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

HE3 suffix meets JESD 201 class 2 whisker test

**Polarity:** as marked

### PRIMARY CHARACTERISTICS

|                       |                               |
|-----------------------|-------------------------------|
| $I_{F(AV)}$           | 2 x 15 A                      |
| $V_{RRM}$             | 35 V, 45 V, 60 V              |
| $I_{FSM}$             | 150 A                         |
| $V_F$                 | 0.54 V, 0.60 V                |
| $I_R$                 | 100 $\mu$ A                   |
| $T_J$ max.            | 175 °C                        |
| Package               | D <sup>2</sup> PAK (TO-263AB) |
| Circuit configuration | Common cathode                |

### MAXIMUM RATINGS ( $T_C = 25$ °C unless otherwise noted)

| PARAMETER                                                                                    | SYMBOL                            | MBRB25H35CT | MBRB25H45CT | MBRB25H60CT | UNIT |
|----------------------------------------------------------------------------------------------|-----------------------------------|-------------|-------------|-------------|------|
| Maximum repetitive peak reverse voltage                                                      | V <sub>RRM</sub>                  | 35          | 45          | 60          | V    |
| Working peak reverse voltage                                                                 | V <sub>RWM</sub>                  | 35          | 45          | 60          |      |
| Maximum DC blocking voltage                                                                  | V <sub>DC</sub>                   | 35          | 45          | 60          |      |
| Max. average forward rectified current (fig. 1) <div>total device<br/>per diode</div>        | I <sub>F(AV)</sub>                | 30          |             |             | A    |
|                                                                                              |                                   | 15          |             |             |      |
| Non-repetitive avalanche energy per diode at 25 °C, I <sub>AS</sub> = 4 A, L = 10 mH         | E <sub>AS</sub>                   | 80          |             |             | mJ   |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode | I <sub>FSM</sub>                  | 150         |             |             | A    |
| Peak repetitive reverse surge current per diode at t <sub>p</sub> = 2.0 μs, 1 kHz            | I <sub>RRM</sub>                  | 1.0         | 1.0         | 0.5         | A    |
| Peak non-repetitive reverse energy (8/20 μs waveform)                                        | E <sub>RSM</sub>                  | 25          | 25          | 20          | mJ   |
| Electrostatic discharge capacitor voltage<br>Human body model: C = 100 pF, R = 1.5 kΩ        | V <sub>C</sub>                    | 25          |             |             | kV   |
| Voltage rate of change (rated V <sub>R</sub> )                                               | dV/dt                             | 10 000      |             |             | V/μs |
| Operating junction and storage temperature range                                             | T <sub>J</sub> , T <sub>STG</sub> | -65 to +175 |             |             | °C   |



| ELECTRICAL CHARACTERISTICS ( $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise noted) |                      |                     |                                     |                            |      |             |      |               |
|-----------------------------------------------------------------------------------------|----------------------|---------------------|-------------------------------------|----------------------------|------|-------------|------|---------------|
| PARAMETER                                                                               | SYMBOL               | TEST CONDITIONS     |                                     | MBRB25H35CT<br>MBRB25H45CT |      | MBRB25H60CT |      | UNIT          |
|                                                                                         |                      |                     |                                     | TYP.                       | MAX. | TYP.        | MAX. |               |
| Maximum instantaneous forward voltage per diode                                         | $V_F$ <sup>(1)</sup> | $I_F = 15\text{ A}$ | $T_J = 25\text{ }^{\circ}\text{C}$  | -                          | 0.64 | -           | 0.70 | V             |
|                                                                                         |                      |                     | $T_J = 125\text{ }^{\circ}\text{C}$ | 0.50                       | 0.54 | 0.56        | 0.60 |               |
|                                                                                         |                      | $I_F = 30\text{ A}$ | $T_J = 25\text{ }^{\circ}\text{C}$  | -                          | 0.74 | -           | 0.85 |               |
|                                                                                         |                      |                     | $T_J = 125\text{ }^{\circ}\text{C}$ | 0.63                       | 0.67 | 0.68        | 0.72 |               |
| Maximum reverse current per diode                                                       | $I_R$ <sup>(2)</sup> | Rated $V_R$         | $T_J = 25\text{ }^{\circ}\text{C}$  | -                          | 100  | -           | 100  | $\mu\text{A}$ |
|                                                                                         |                      |                     | $T_J = 125\text{ }^{\circ}\text{C}$ | 6.0                        | 20   | 4.0         | 20   | mA            |

**Notes**<sup>(1)</sup> Pulse test: 300  $\mu\text{s}$  pulse width, 1 % duty cycle<sup>(2)</sup> Pulse test: pulse width  $\leq 40\text{ ms}$ 

| THERMAL CHARACTERISTICS ( $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise noted) |                 |      |                      |
|--------------------------------------------------------------------------------------|-----------------|------|----------------------|
| PARAMETER                                                                            | SYMBOL          | MBRB | UNIT                 |
| Thermal resistance, junction to case per diode                                       | $R_{\theta JC}$ | 1.5  | $^{\circ}\text{C/W}$ |

| ORDERING INFORMATION (Example) |                                   |                 |              |               |               |
|--------------------------------|-----------------------------------|-----------------|--------------|---------------|---------------|
| PACKAGE                        | PREFERRED P/N                     | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |
| TO-263AB                       | MBRB25H60CTHE3_B/P <sup>(1)</sup> | 1.35            | P            | 50/tube       | Tube          |
| TO-263AB                       | MBRB25H60CTHE3_B/I <sup>(1)</sup> | 1.35            | I            | 800/reel      | Tape and reel |

**Note**<sup>(1)</sup> AEC-Q101 qualified



## RATINGS AND CHARACTERISTICS CURVES ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

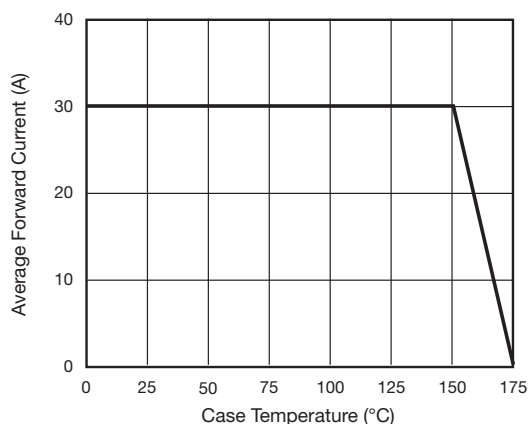


Fig. 1 - Forward Derating Curve (Total)

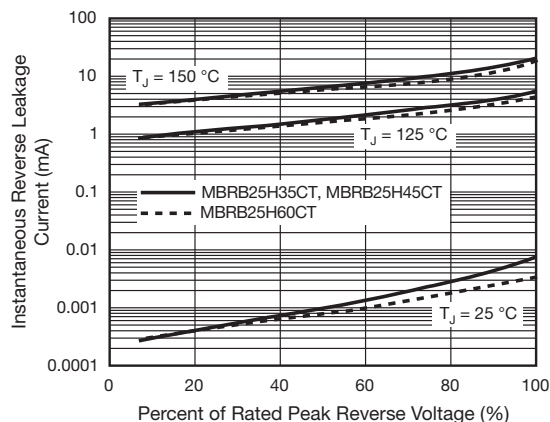


Fig. 4 - Typical Reverse Characteristics Per Diode

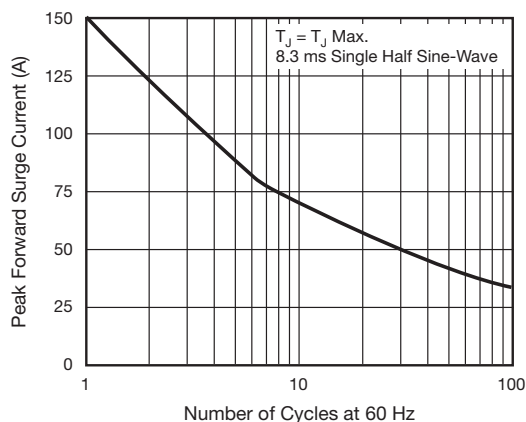


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

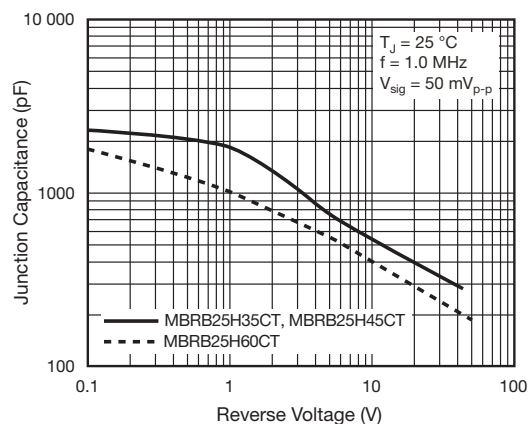


Fig. 5 - Typical Junction Capacitance Per Diode

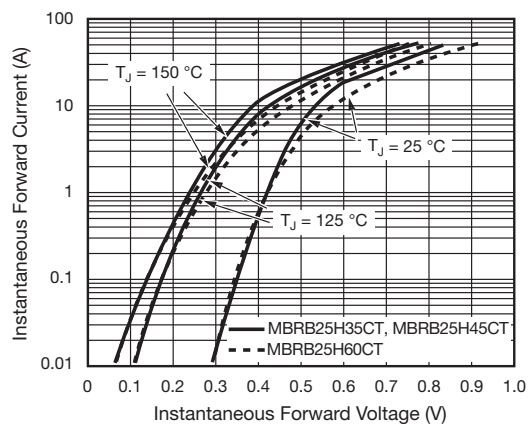


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

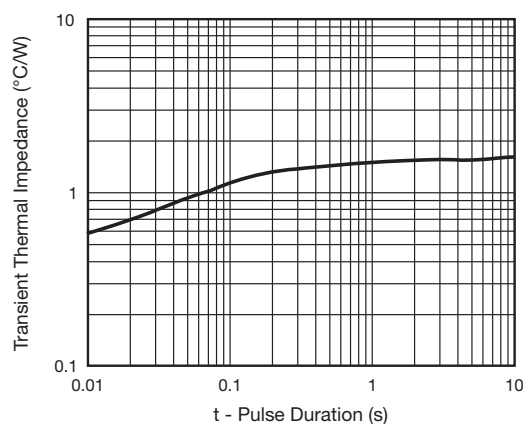
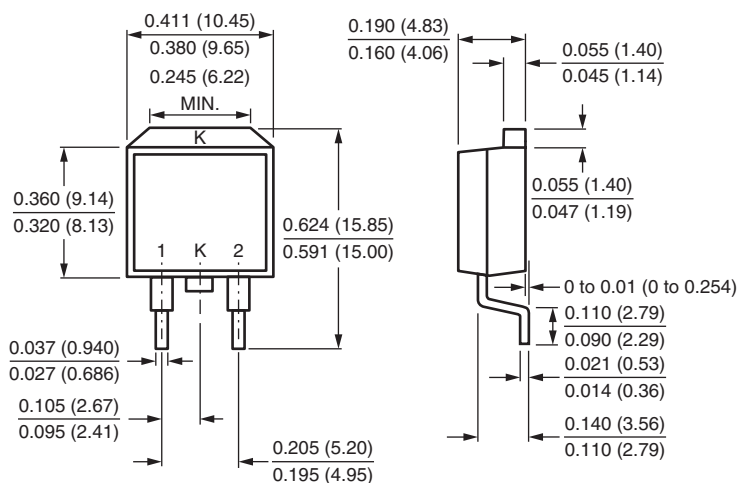


Fig. 6 - Typical Transient Thermal Impedance Per Diode

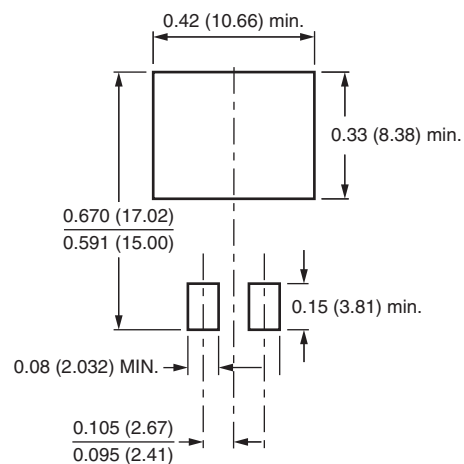


**PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)

**D<sup>2</sup>PAK (TO-263AB)**



**Mounting Pad Layout**





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